

MA3U760

Silicon epitaxial planar type (cathode common)

For switching power supply

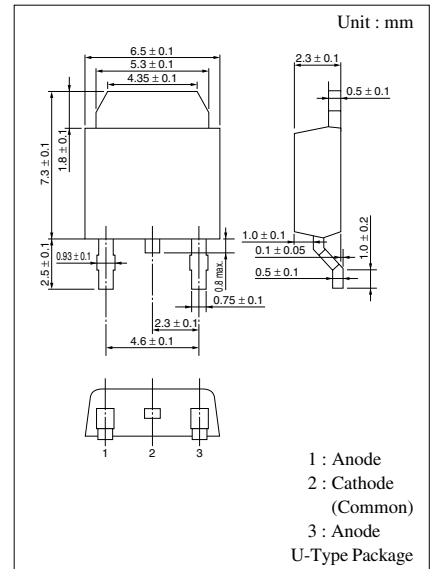
■ Features

- Small U-type package and surface mounting
- High breakdown voltage V_R
- Low forward rise voltage V_F
- Cathode common dual type

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|--|-------------|-------------|------------------|
| Repetitive peak reverse voltage | V_{RRM} | 90 | V |
| Average forward current | $I_{F(AV)}$ | 5 | A |
| Non-repetitive peak forward surge current* | I_{FSM} | 40 | A |
| Junction temperature | T_j | -40 to +125 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -40 to +125 | $^\circ\text{C}$ |

Note) * : Half sine-wave: 10 ms/cycle



■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|----------------------|---------------|---|-----|-----|------|---------------------------|
| Reverse current (DC) | I_R | $V_R = 90\text{ V}$, $T_C = 25^\circ\text{C}$ | | | 1.0 | mA |
| Forward voltage (DC) | V_F | $I_F = 2.5\text{ A}$, $T_C = 25^\circ\text{C}$ | | | 0.85 | V |
| Thermal resistance* | $R_{th(j-c)}$ | Between junction and case | | | 12.5 | $^\circ\text{C}/\text{W}$ |

Note) 1. Rated input/output frequency: 1 000 MHz

2. * : $T_C = 25^\circ\text{C}$

